

Abstract

Memory arrangement and method for operating such a memory arrangement

In the memory arrangement according to the invention, rewritable memory cells (MC) are arranged at crossovers between word lines (WL) and bit lines (BL), said memory cells being configured in such a manner that the information stored in them is essentially read out in a nondestructive manner. According to the invention, the memory arrangement has a flag cell (MMC) either for each word line (WL) or for each bit line (BL), said flag cell being able to store an item of information that indicates whether at least one of the memory cells (MC) either along the respective word line (WL) or along the respective bit line (BL) has been subjected to a reading operation since a basic state occurred.

(Fig. 1)